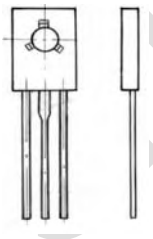
BD233/235/237 TRANSISTOR (NPN)



FEATURES

Power dissipation

$P_{CM:}$ 1.25 W (Tamb=25℃)

Collector current

$I_{CM:}$ 2 A

Collector-base voltage

$V_{(BR)CBO}$: BD233 : 45 V

BD235: 60 V

BD237: 100 V

Operating and storage junction temperature range

$T_{J:}$ 150℃

T_{stg}: -65℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage **BD233**	$V(BR)_{CBO}$	Ic= 100μA, I_E=0	45		V
BD235			60		
BD237			100		
Collector-emitter breakdown voltage **BD233**	$V(BR)_{CEO}$	Ic= 10mA, I_B=0	45		V
BD235			60		
BD237			80		
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100μA, I_C=0	5		V
Collector cut-off current **BD233**	I_{CBO}	V_{CB}= 45V, I_E=0		100	μA
BD235		V_{CB}= 60V, I_E=0			
BD237		V_{CB}= 100V, I_E=0			
Emitter cut-off current	I_{EBO}	V_{EB}= 5V, I_C=0		1	mA
DC current gain	$H_{FE(1)}$	V_{CE}= 2V, I_C=150mA	40		
	$H_{FE(2)}$	V_{CE}=2V, I_C= 1A	25		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=1A, I_B= 100m A		0.6	V
Transition frequency	f_T	V_{CE}=10V, Ic=250mA f =10MHz	3		MHz